

Amendment to the Specification

Change paragraph 0004, as follows:

[0004] Consequently, a new type of circuit design model named HiSIM (Hiroshima-university STARC IGFET Model) which is a surface potential model wherein a formula for analysis is derived based on surface potential, has been recently developed and disclosed by Miura, one of the inventors of the present invention. The HiSIM wherein the transistor property is described by using the surface potential has a small number of parameters compared to the conventional BSIM which is indicated as a function of an external voltage, and even if the HiSIM is extrapolated, a high-accuracy simulation can be performed. Incidentally, since details of the HiSIM and conventional parameter adjusting means in the HiSIM are described in the following publication available for downloading from the following URL, detailed explanations are omitted.

Japanese Nonpatent Publication 1: HiSIM 1.1.1 User's Manual

~~URL: <http://www.starc.or.jp/kaihatu/pdgr/hisim/hisim.html>~~